

MAXIMUM RATINGS: ($T_A=25^\circ\text{C}$)

	SYMBOL		UNITS
Continuous Reverse Voltage	V_R	75	V
Peak Repetitive Reverse Voltage	V_{RRM}	85	V
Continuous Forward Current	I_F	250	mA
Peak Repetitive Forward Current	I_{FRM}	500	mA
Forward Surge Current, $t_p=1 \mu\text{s}$	I_{FSM}	4.0	A
Forward Surge Current, $t_p=1 \text{ ms}$	I_{FSM}	2.0	A
Forward Surge Current, $t_p=1 \text{ s}$	I_{FSM}	1.0	A
Power Dissipation	P_D	350	mW
Operating and Storage			
Junction Temperature	T_J, T_{stg}	-65 to +150	$^\circ\text{C}$
Thermal Resistance	Θ_{JA}	357	$^\circ\text{C/W}$

ELECTRICAL CHARACTERISTICS PER DIODE: ($T_A=25^\circ\text{C}$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
I_R	$V_R=25\text{V}, T_A=150^\circ\text{C}$		30	μA
I_R	$V_R=75\text{V}$		1.0	μA
I_R	$V_R=75\text{V}, T_A=150^\circ\text{C}$		50	μA
BV_R	$I_R=100\mu\text{A}$	85		V
V_F	$I_F=1.0\text{mA}$		715	mV
V_F	$I_F=10\text{mA}$		855	mV
V_F	$I_F=50\text{mA}$		1.00	V
V_F	$I_F=150\text{mA}$		1.25	V
C_T	$V_R=0, f=1.0 \text{ MHz}$		2.0	pF
t_{rr}	$I_F=I_R=10\text{mA}, R_L=100\Omega, \text{Rec. to } 1.0\text{mA}$		6.0	ns

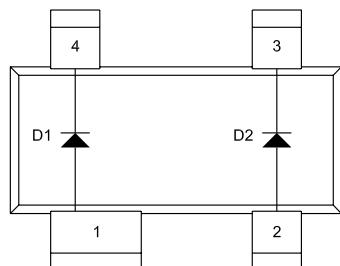
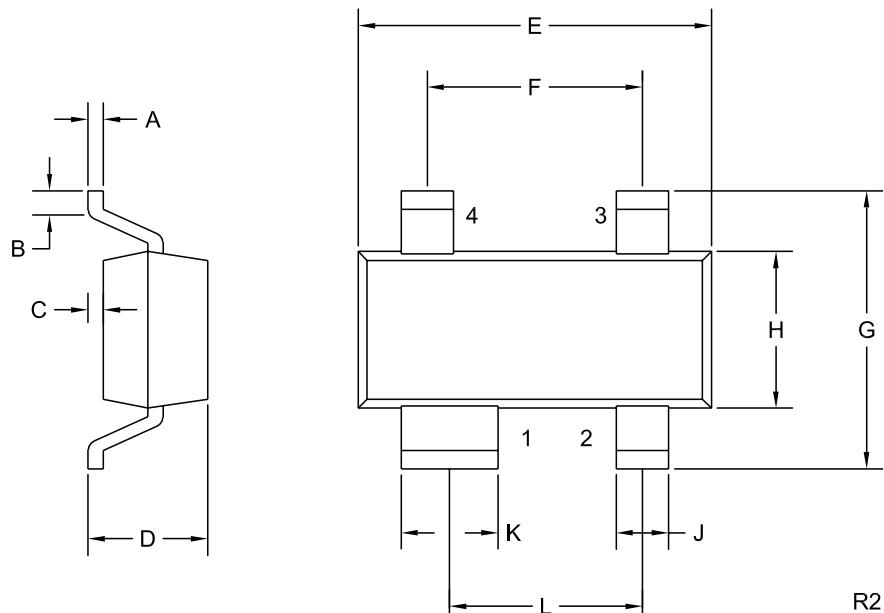
CentralTM
Semiconductor Corp.

DESCRIPTION:

The CENTRAL SEMICONDUCTOR BAW100 consists of two electrically isolated high speed silicon switching diodes packaged in an epoxy molded SOT-143 surface mount case. This device is designed for high speed switching applications.

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SOT-143 CASE - MECHANICAL OUTLINE



LEAD CODE:

- 1) ANODE D1
- 2) ANODE D2
- 3) CATHODE D2
- 4) CATHODE D1

SYMBOL	DIMENSIONS			
	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.003	0.006	0.08	0.15
B	0.006	-	0.15	-
C	-	0.005	-	0.13
D	-	0.045	-	1.14
E	0.110	0.120	2.79	3.04
F	0.075	-	1.90	-
G	-	0.098	-	2.50
H	0.047	0.055	1.19	1.40
J	0.014	0.020	0.36	0.50
K	0.030	0.037	0.76	0.93
L	0.067	-	1.70	-

SOT-143 (REV: R2)

MARKING CODE: CJSS

R2 (3-December 2003)